ABSTRACT

HIGH RESISTIVITY SINGLE CRYSTAL SILICON INGOT AND WAFER HAVING IMPROVED MECHANICAL STRENGTH

A method for preparing a single crystal silicon ingot and a wafer sliced therefrom are provided. The ingots and wafers comprise nitrogen at a concentration of at least about $1x10^{14}$ atoms/cm^3 and/or germanium at a concentration of at least about $1x10^{19}$ atoms/cm^3, interstitial oxygen at a concentration of less than about 6 ppma, and a resistivity of at least about 1000 ohm cm.

FIG. 11